L Number	Hits	Search Text	DB	Time stamp
-	35	(((((257/295,298,310,532).CCLS.) and buried near3 contact) and ferroelectric) and contact adj hole) and ((silicon adj oxynitride) or (silicon adj nitride))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/17 17:41
-	6203	(438/3,253,254,238,396).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/17 17:47
-	64	((438/3,253,254,238,396).CCLS.) and buried near3 contact and ferroelectric and contact adj hole	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/17 17:48
-	1	((257/295,298,310,532).CCLS.) and (insulat$3 and substrate and contact adj hole and (burry or burried))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/02 16:55
-	0	((438/3,253,254,238,396).CCLS.) and (insulat$3 and substrate and contact adj hole and (burry or burried))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/02 16:56
-	5458	(257/295,296,298,310,532).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/02 16:56
-	5458	(257/295,296,298,310,532).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/02 16:56
-	6492	(438/3,253,254,238,396).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/02 16:56
-	1586	(ferroelectric adj memory) and (insulat$3 and substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/02 16:57
-	46	insulat$3 and substrate and contact adj hole and (burry or burried)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/02 16:57
-	66	((((((blocking adj layer) (etch adj stop)) with ((silicon adj nitride) (silicon adj oxinitride) (aluminum adj oxide) "SiOn" "SiN" "AlO"))) and dram) and capacitor) and ferroelectric	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 07:51
-	5	((((((blocking adj layer) (etch adj stop)) with ((silicon adj nitride) (silicon adj oxinitride) (aluminum adj oxide) "SiOn" "SiN" "AlO"))) and dram) and capacitor) and ferroelectric and electrode with metallic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 07:52

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